

140 COMMERCE DRIVE MONTGOMERYVILLE, PA 18936-1013

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## **MS2422**

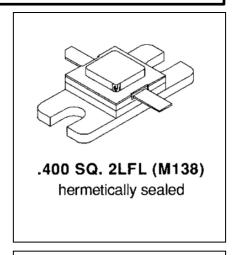
## RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

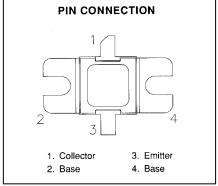
## **Features**

- DESIGNED FOR HIGH POWER PULSED IFF, DME, AND TACAN APPLICATIONS
- 350 W (typ.) IFF 1030 1090 MHz
- 300 W (min.) DME 1025 1150 MHz
- 290 W (typ.) TACAN 960 1215 MHz
- 960 1215 MHz
- GOLD METALLIZATION
- P<sub>OUT</sub> = 300W MINIMUM
- $G_P = 6.3 \text{ dB MINIMUM}$
- INFINITE VSWR CAPABILITY @ RATED CONDITIONS
- EMITTER BALLASTED
- COMMON BASE

## **DESCRIPTION:**

The MS2422 is a gold metallized silicon, NPN power transistor designed for applications requiring high peak power and low duty cycles such as IFF, DME, and TACAN. The MS2422 is designed with internal input/output matching resulting in improved broadband performance and low thermal resistance.





## **ABSOLUTE MAXIMUM RATINGS (Tcase = 25^{\circ}C)**

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	65	V
V <sub>CES</sub>	Collector-Emitter Voltage	65	V
V <sub>EBO</sub>	Emitter-Base Voltage	3.5	V
I <sub>C</sub>	Device Current	22	Α
P <sub>DISS</sub>	Power Dissipation	875	W
TJ	Junction Temperature	200	°C
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C

## **Thermal Data**

R <sub>TH(J-C)</sub> Junction-case Thermal Resistance	0.20	°C/W
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**MS2422** 

# **ELECTRICAL SPECIFICATIONS (Tcase = 25°C) STATIC**

Symbol		Test Conditions		Value Min. Typ. Max.		Unit
		rest Conditions	Min.		Offic	
BV <sub>CBO</sub>	I <sub>C</sub> = 10 mA	I <sub>E</sub> = 0 mA	65			V
BV <sub>CES</sub>	I <sub>C</sub> = 25 mA	$V_{BE} = 0 V$	65			V
$BV_{EBO}$	I <sub>E</sub> = 5.0 mA	$I_C = 0 \text{ mA}$	3.5			V
I <sub>CES</sub>	V <sub>CE</sub> = 50 V	I <sub>E</sub> = 0 mA			25	mA
h <sub>FE</sub>	V <sub>CE</sub> = 5 V	I <sub>C</sub> = 1A	10			mA

## **DYNAMIC**

Symbol	Test Conditions		Value			Unit
Syllibol			Min.	Тур.	Max.	
P <sub>out</sub>	f = 1025 - 1150 MHz P <sub>IN</sub> = 70W	V <sub>CE</sub> = 50V	300			W
G <sub>P</sub>	f = 1025 - 1150 MHz P <sub>IN</sub> = 70W	V <sub>CE</sub> = 50V	6.3			dB
ης	f = 1025 - 1150 MHz P <sub>IN</sub> = 70W	V <sub>CE</sub> = 50V	35			%
Conditions	Pulse Width = 10 μs Duty Cycle = 1%					

## **IMPEDANCE DATA**

FREQ	$Z_{IN}(\Omega)$	$Z_{\mathtt{CL}}\!\left(\Omega ight)$
960 MHz	5.1 + j1.0	2.2 – j3.5
1090 MHz	4.2 + j0.5	2.5 – j3.5
1215 MHz	7.5 + j1.5	2.3 – j1.5

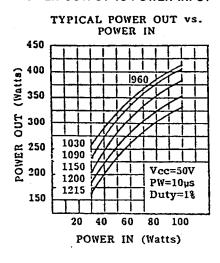
Pin = 70W Vce = 50V



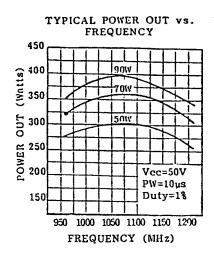


## **TYPICAL PERFORMANCE**

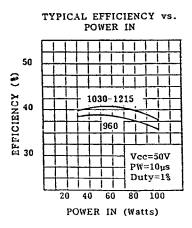
#### POWER OUTPUT vs POWER INPUT



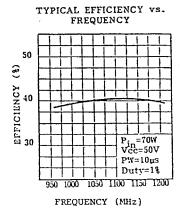
## POWER OUTPUT vs FREQUENCY



## **EFFICIENCY vs POWER INPUT**



## **EFFICIENCY vs FREQUENCY**

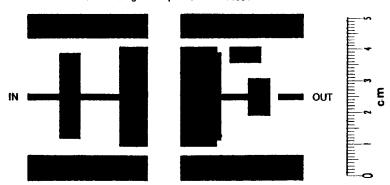


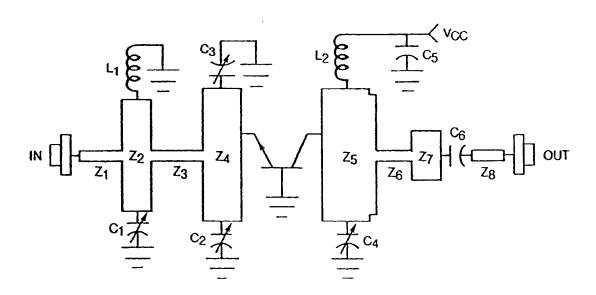




## **TEST CIRCUIT**

Teflon Fiberglass  $\mathcal{E}_{f} = 2.5$  THK .031





## All Dimension are in Inches

C1,C2.	Z1	: .404 x .075
C3, C4: .6 - 4.5pF JOHANSON Gigatrim	Z2	: .263 x .995
C5 : 1000μF, 63V, Electrolytic	Z3	: .483 x .077
C6 : 100pF Chip Capacitor Across .090 Gap	<b>Z</b> 4	: .350 x 1.203
	75	. FOE .: 1 000

L1 : 2 Turns #24 .12 I.D., Spaced Wire Diameter
L2 : 4 Turns #24, .07 I.D., Spaced Wire Diameter
L2 : 3 Turns #24, .07 I.D., Spaced Wire Diameter
L2 : 4 Turns #24, .07 I.D., Spaced Wire Diameter
L3 : .505 x 1.200 with Two Notches .05 Long
By .068 Wide
.335 x .076

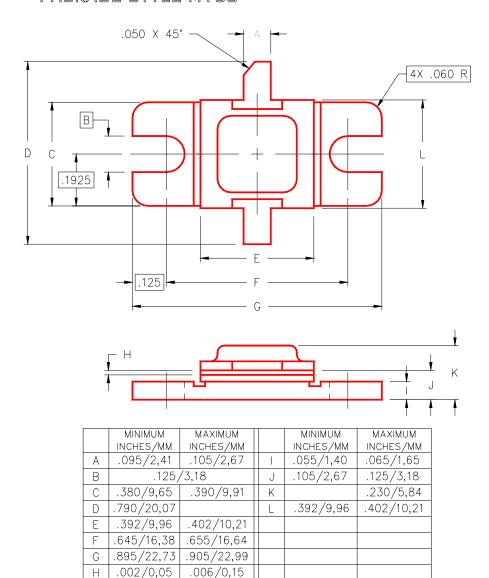
Z6 : .335 x .076 Z7 : .260 x .442 Z8 : .310 x .082





## **PACKAGE MECHANICAL DATA**

## PACKAGE STYLE M138



# AMEYA360 Components Supply Platform

## **Authorized Distribution Brand:**

























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